Abstracts

New Aspects Concerning the Bias and Temperature Dependence of Intrinsic Noise Generators in Extracted FET Models

S.M. Lardizabal, L.P. Dunleavy and A. Boudiaf. "New Aspects Concerning the Bias and Temperature Dependence of Intrinsic Noise Generators in Extracted FET Models." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1325-1328.

A systematic experimental investigation of FET noise models illustrates bias and temperature dependencies that help to explain differences between two prevalent models. Observations concerning the bias dependence of the popular temperature based noise model show that the gate noise temperature follows the ambient temperature only near the minimum noise bias condition.

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